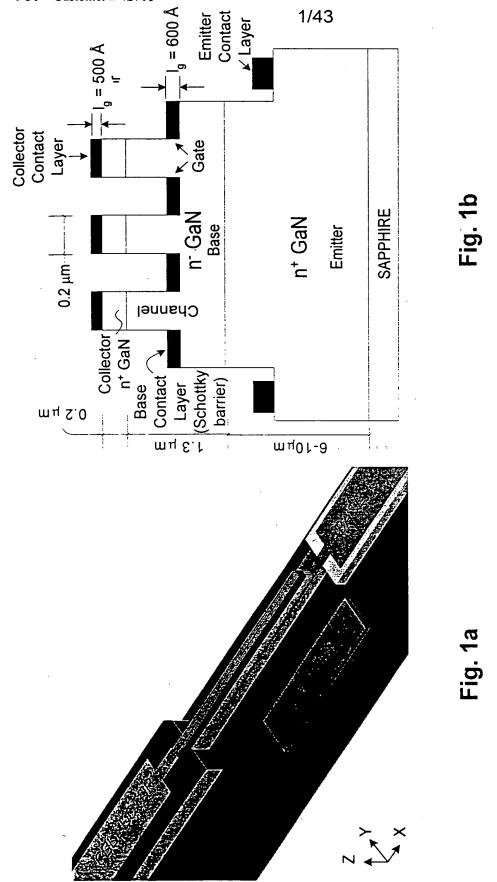
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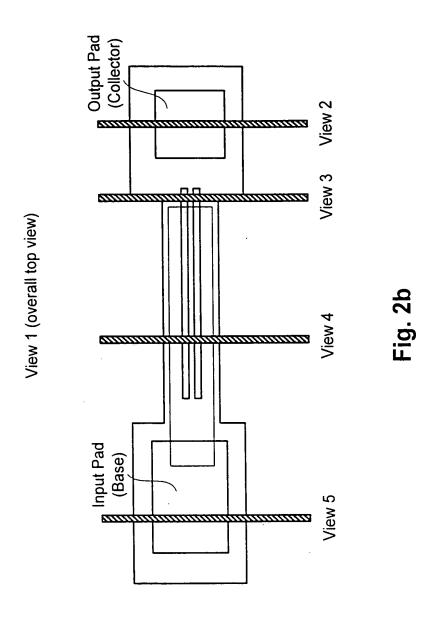
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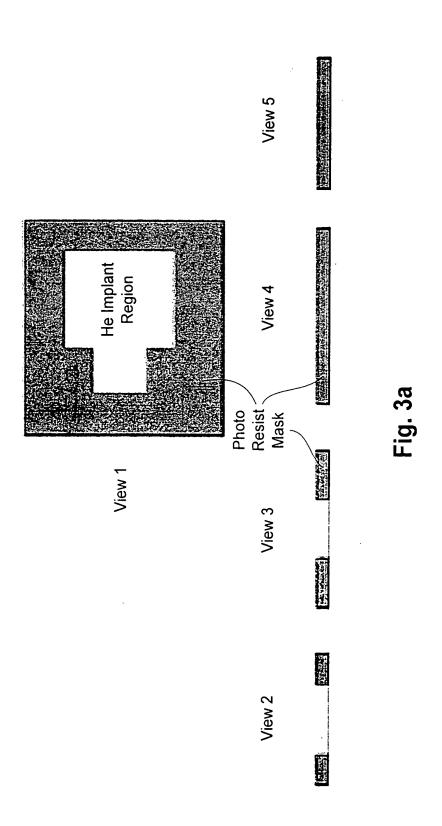
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0.3 µm	2 µm	10 µm
n ⁺ GaN (5 x 10 ¹⁸ cm ⁻³) MBE	n ⁻ GaN (5 x 10 ¹⁶ cm ⁻³) MBE	n⁺ GaN (5 x 10¹ ⁸ cm⁻³) HVPE

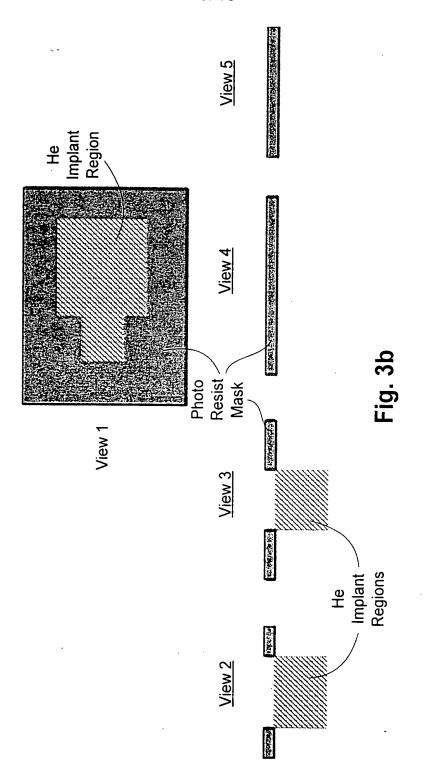
Fig. 2a



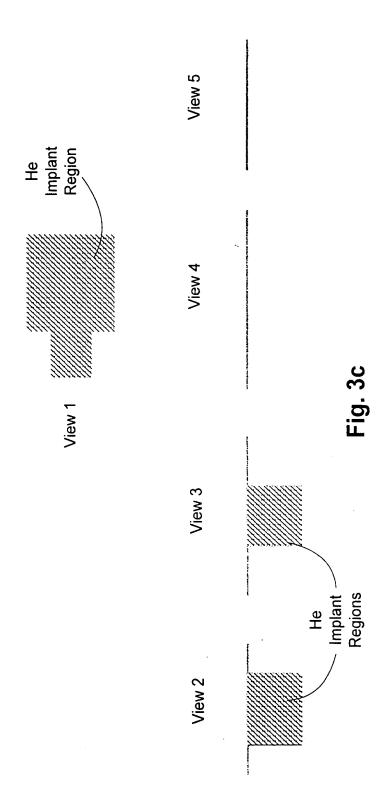
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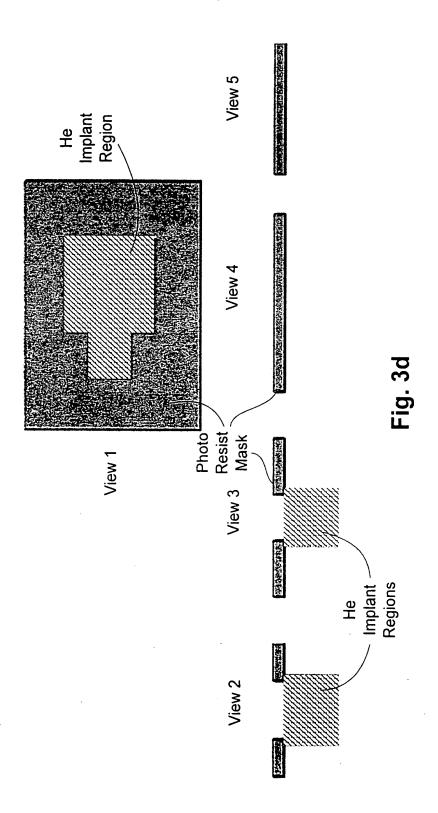
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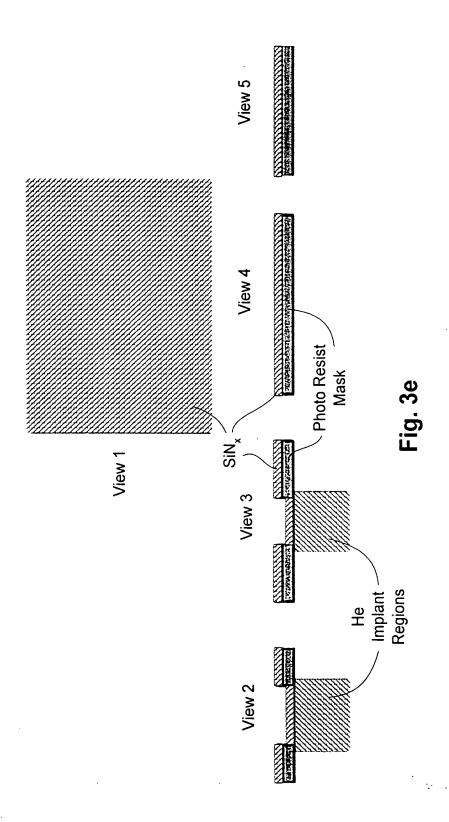
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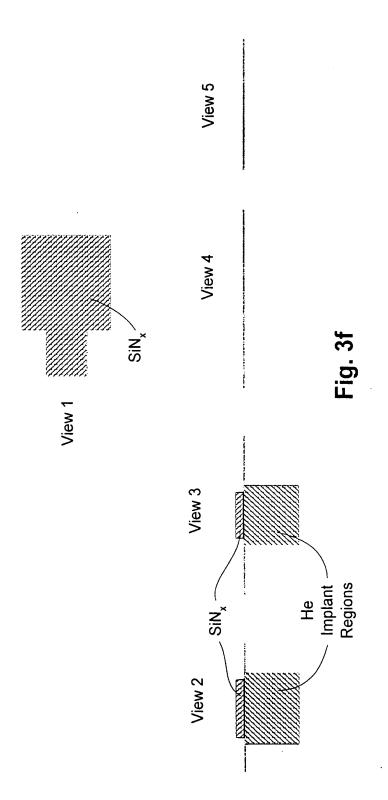
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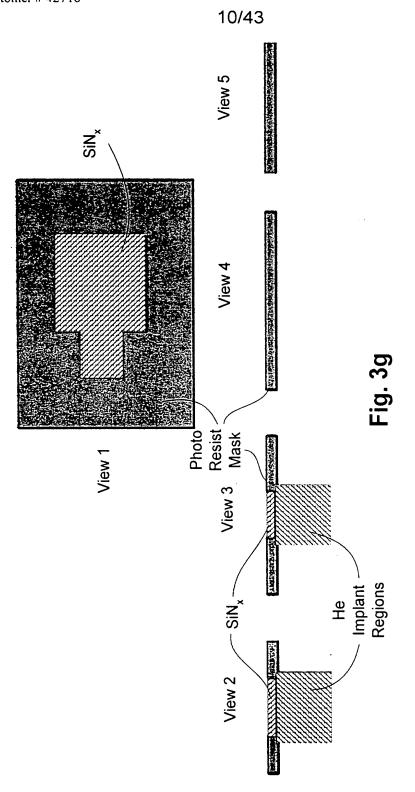
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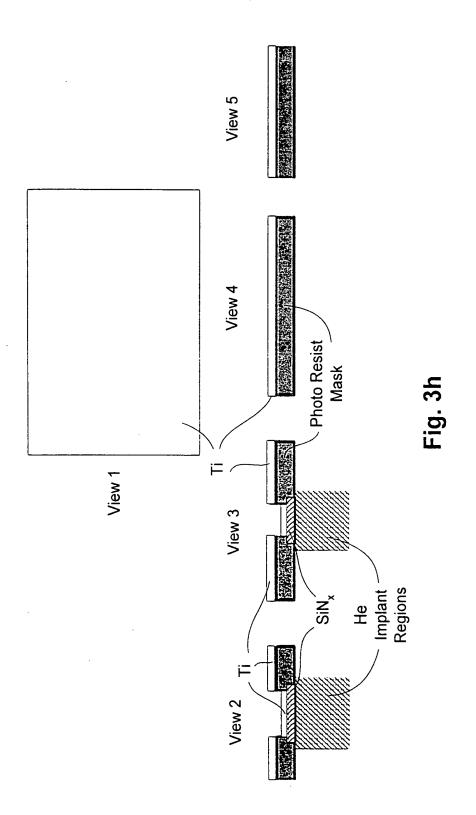
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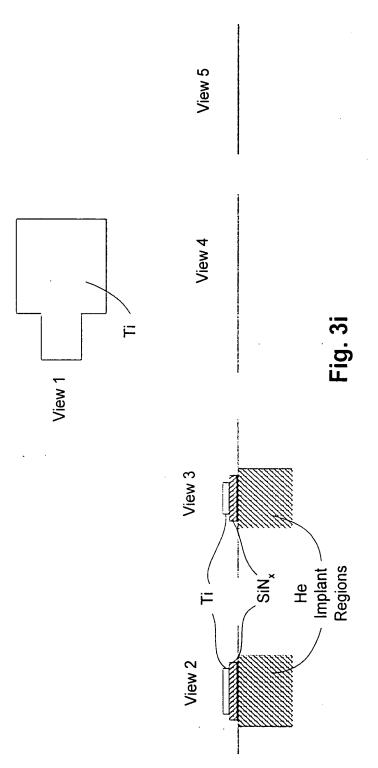
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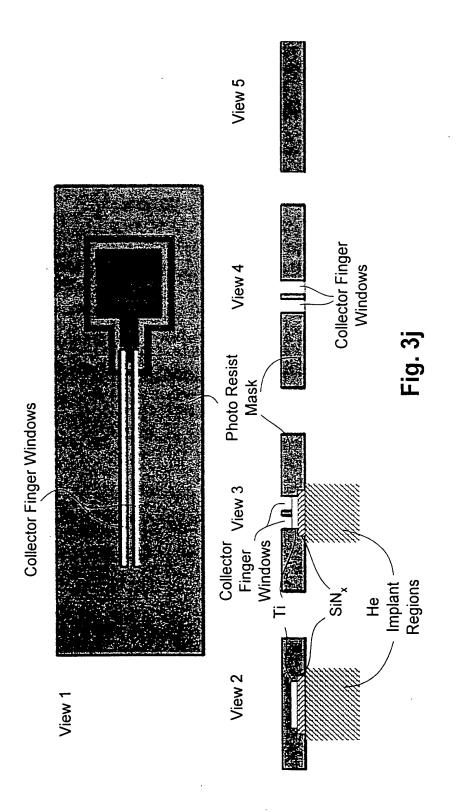
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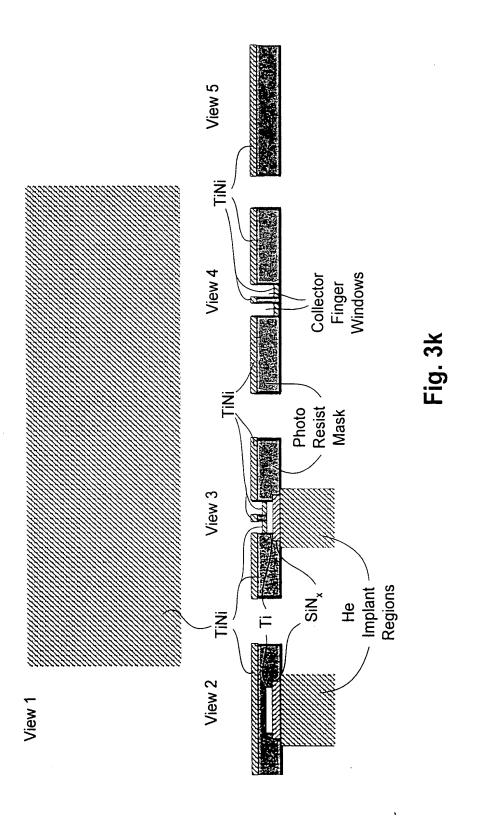


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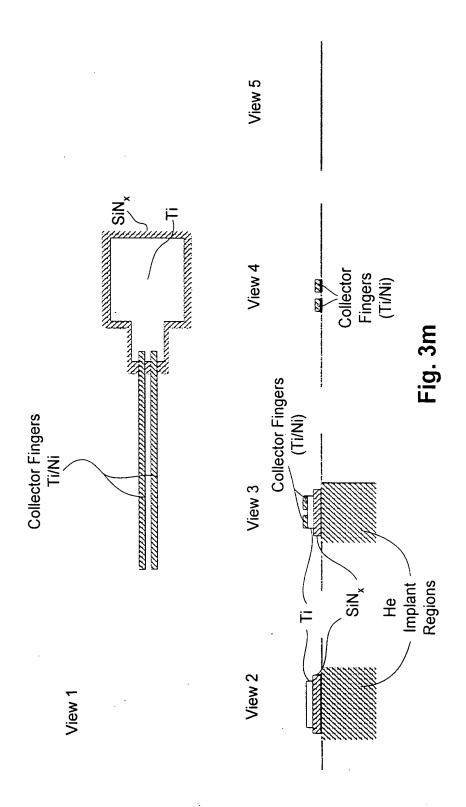


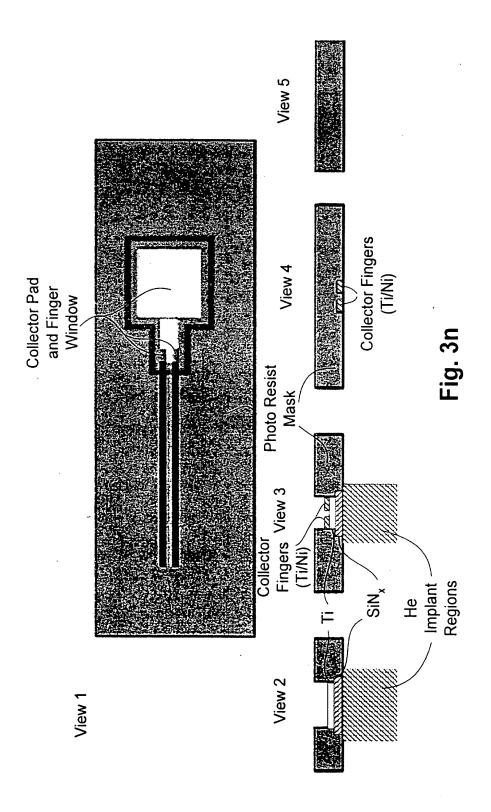
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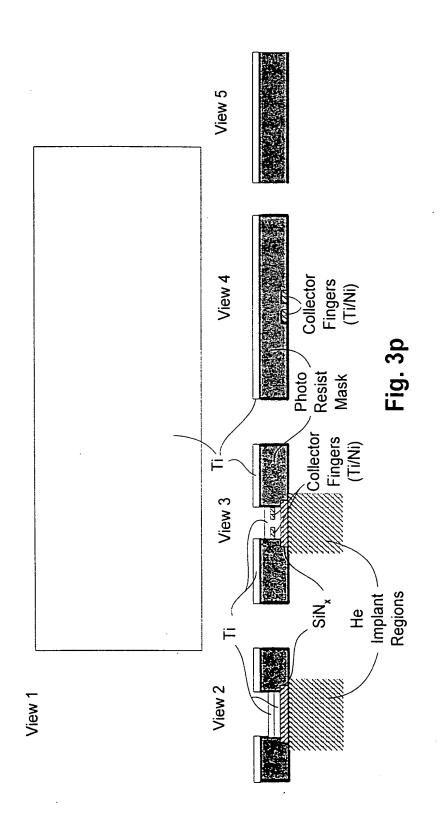


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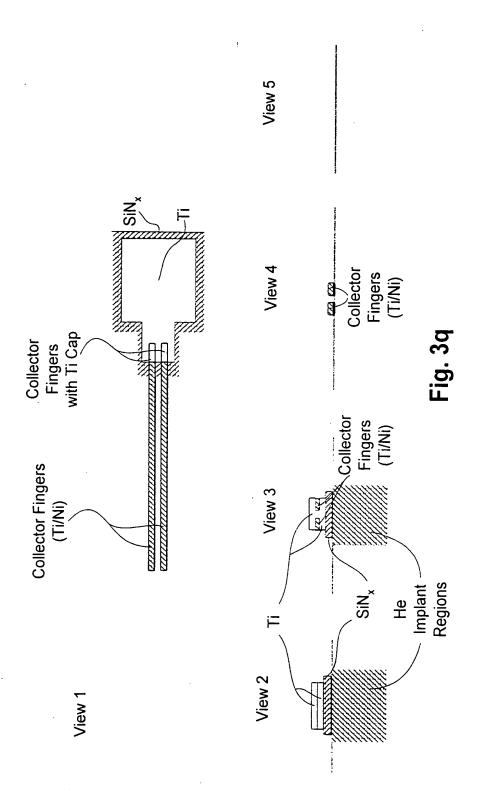




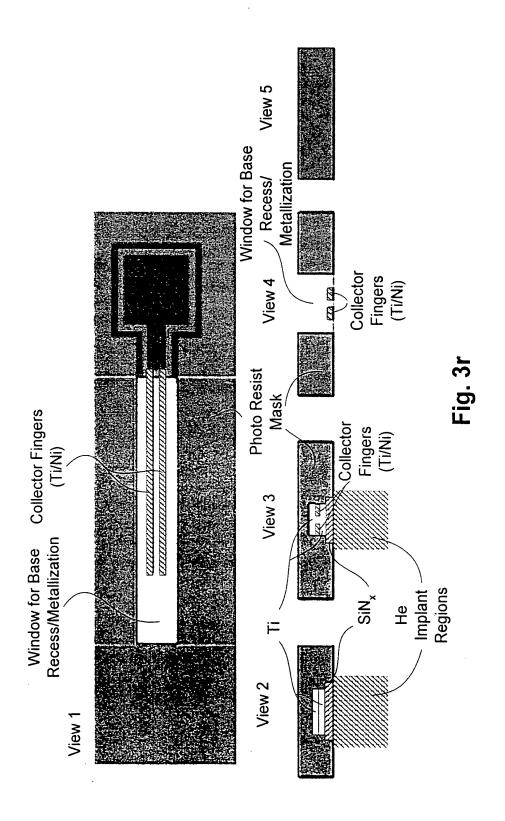
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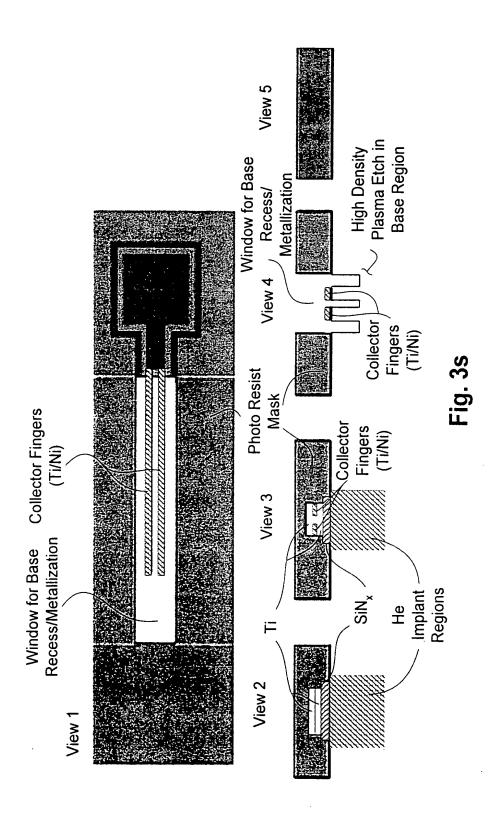
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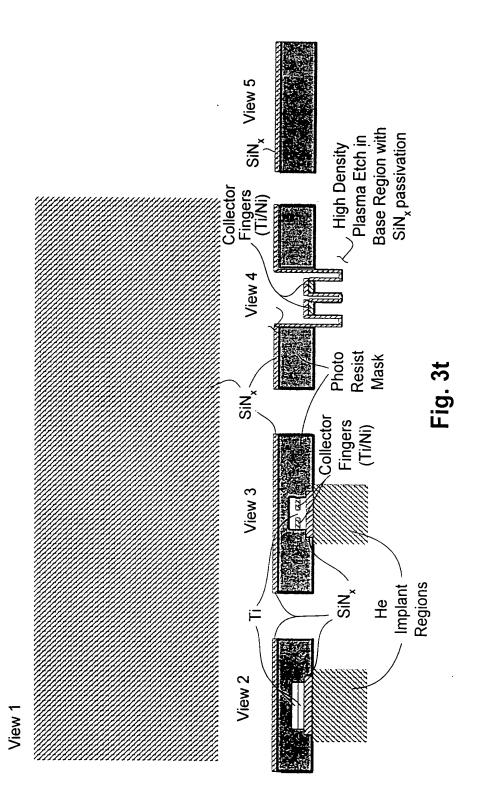
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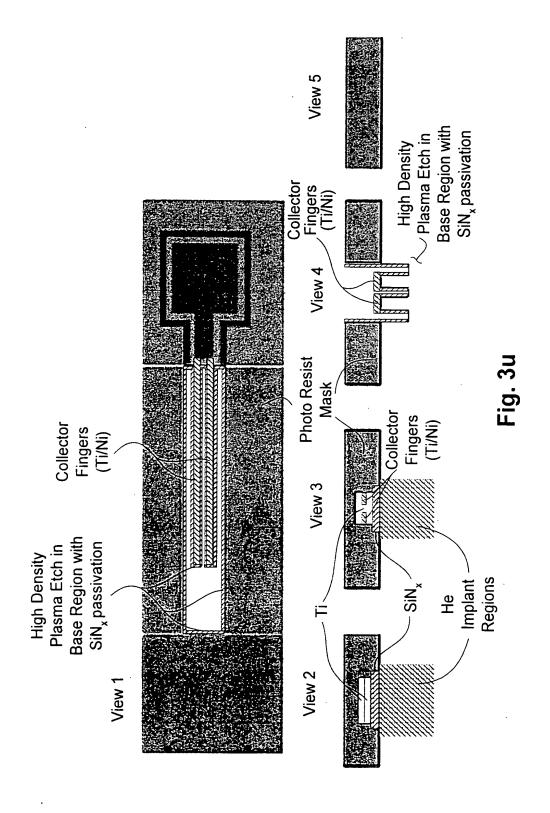
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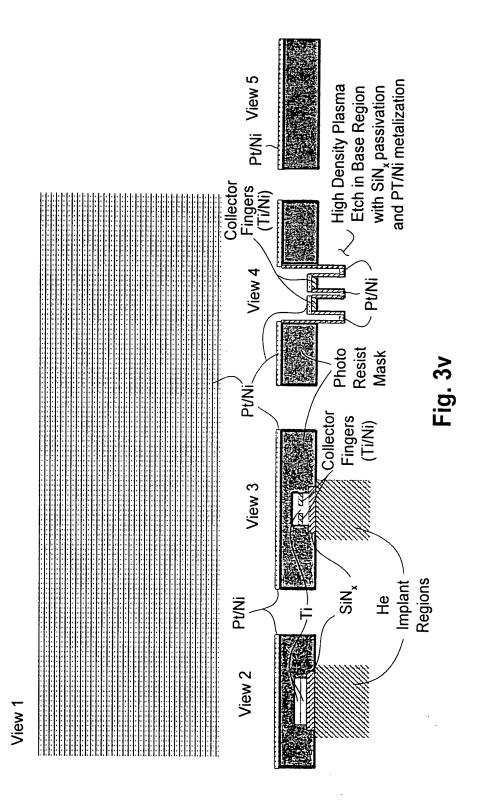
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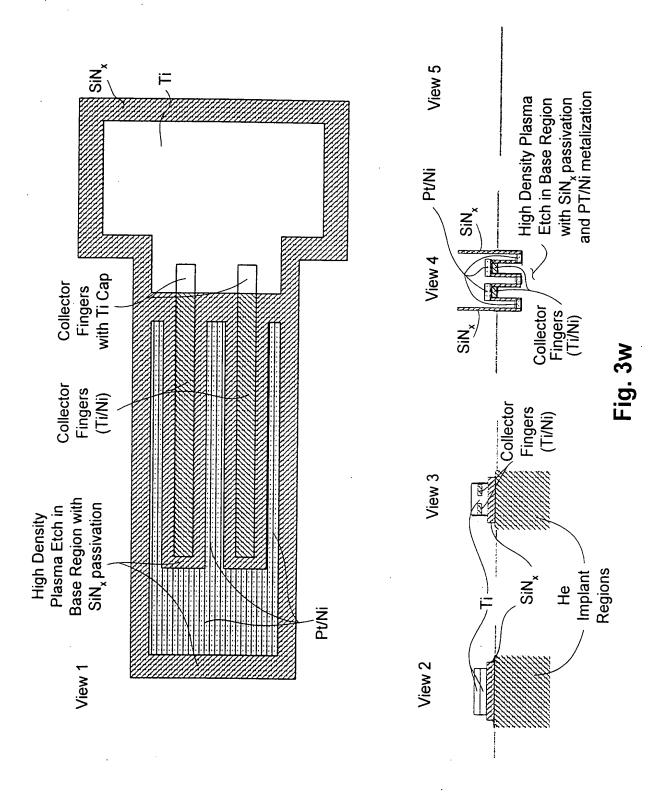
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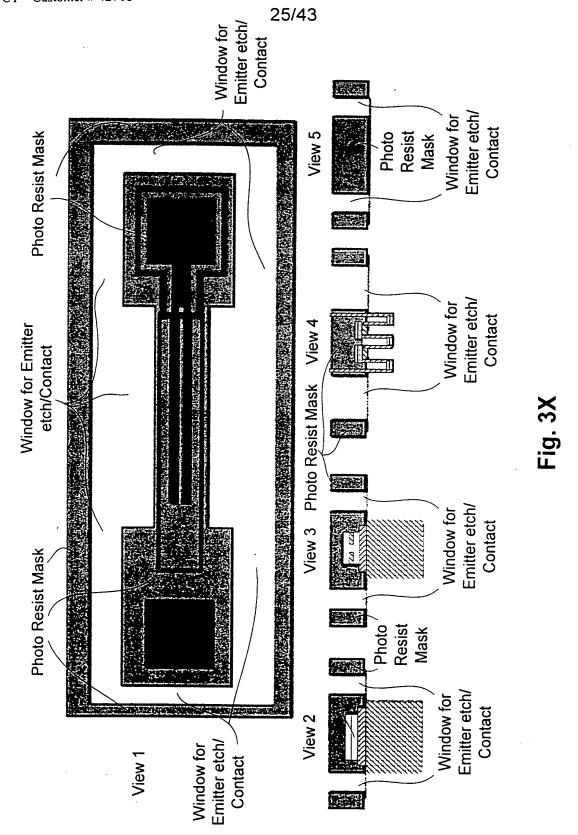
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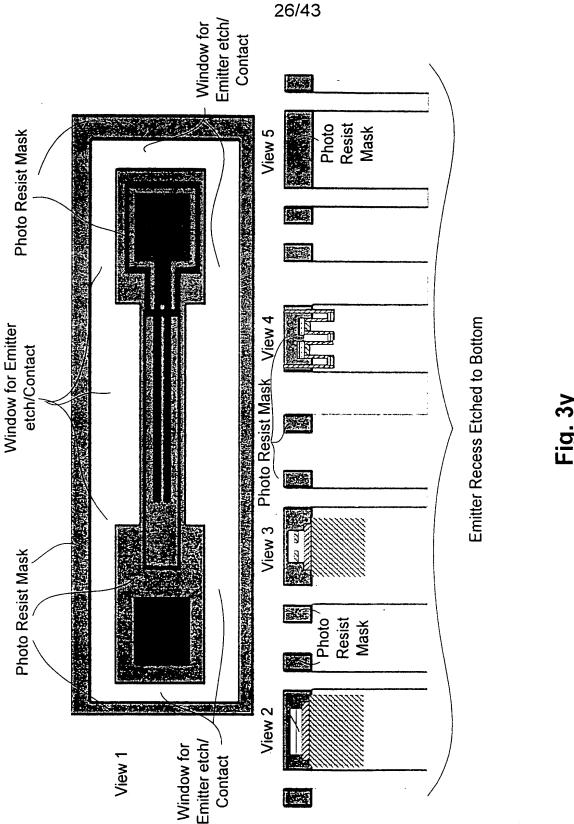
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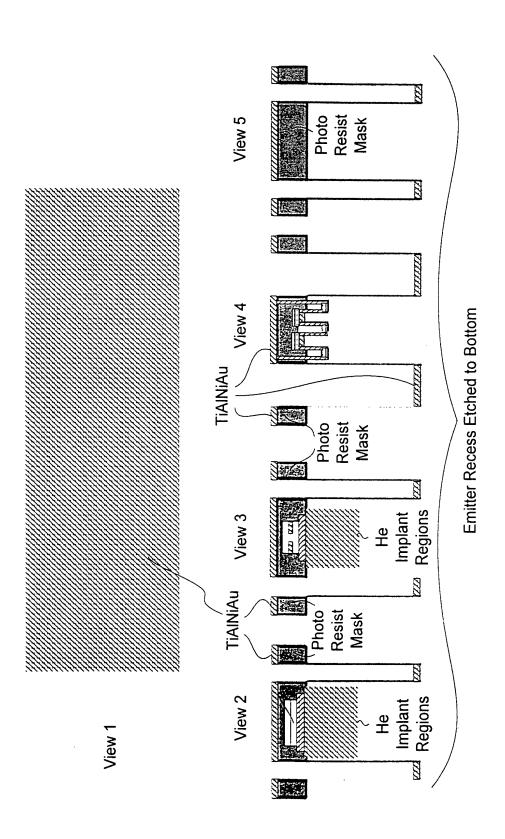
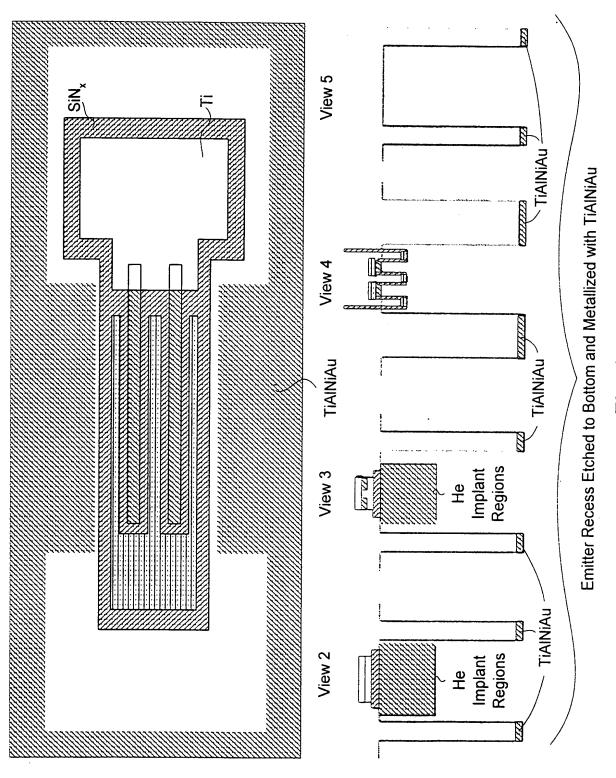


Fig. 3z

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View 1

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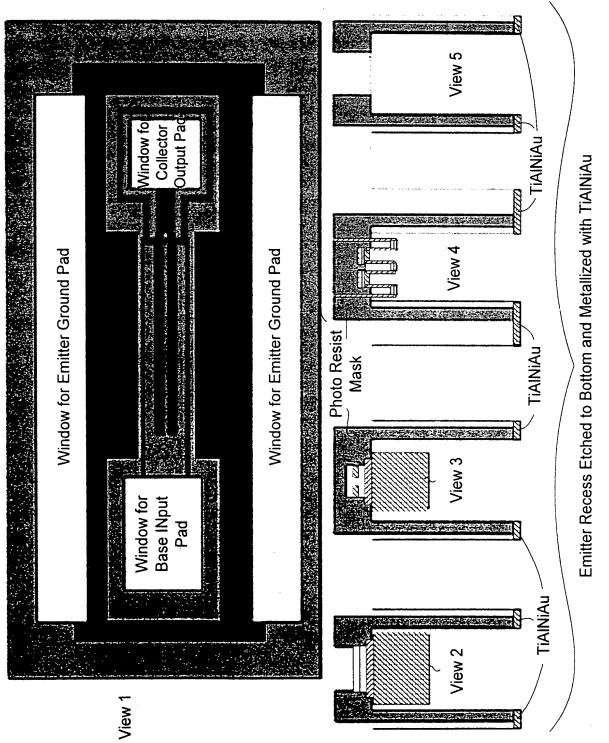


Fig. 3bb

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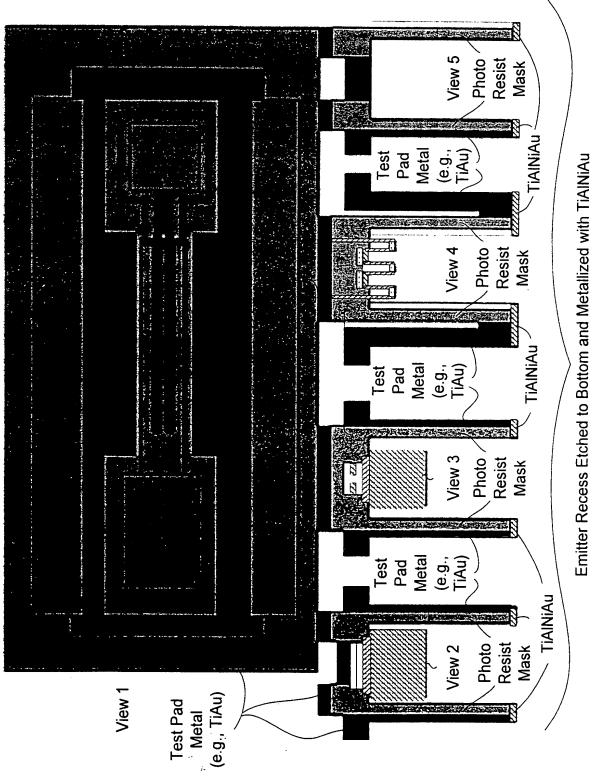
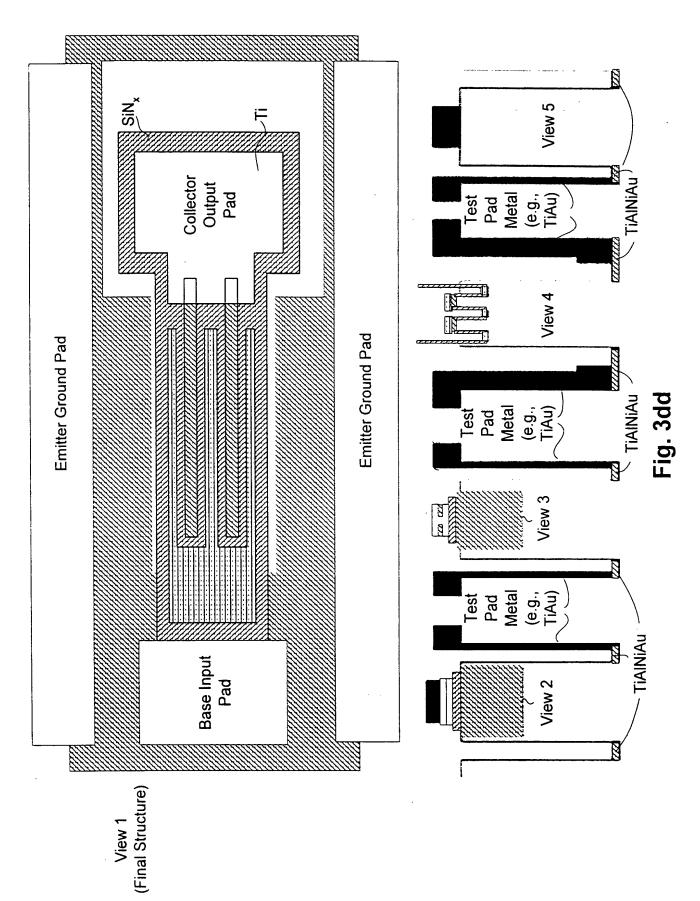


Fig. 3cc

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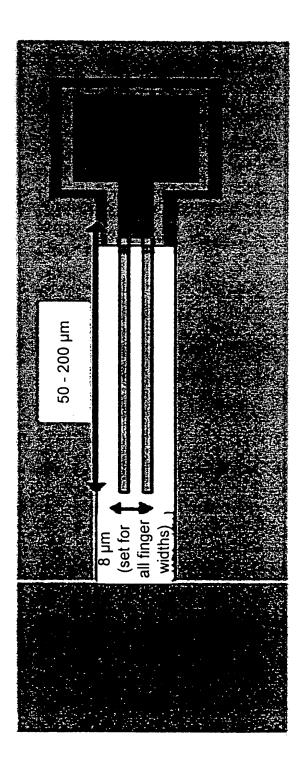
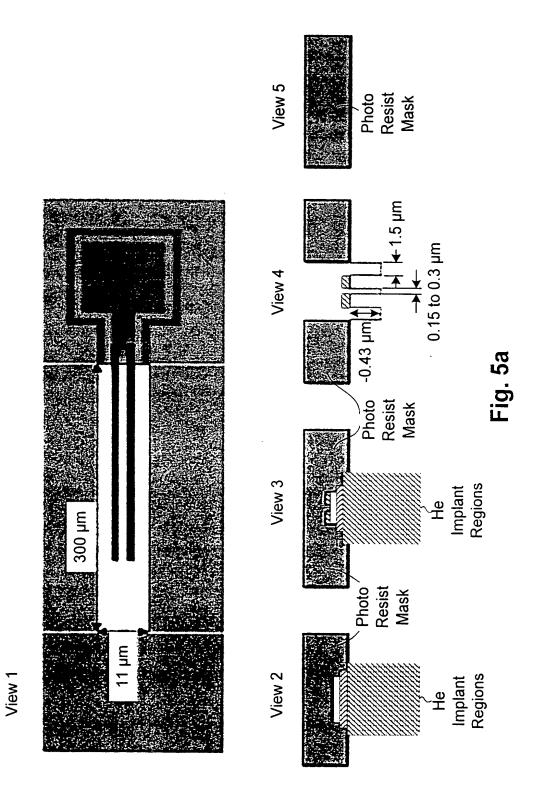


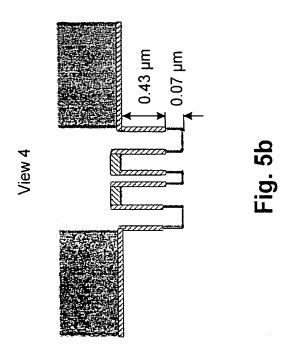
Fig. 4

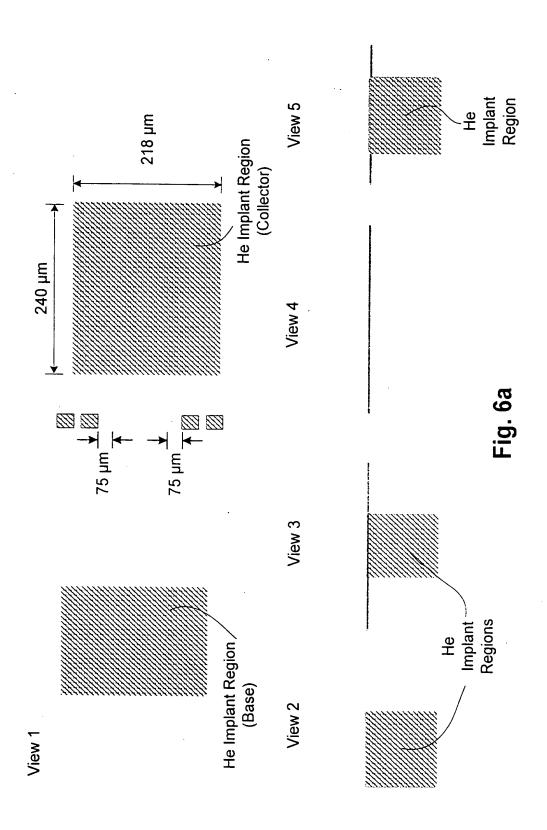
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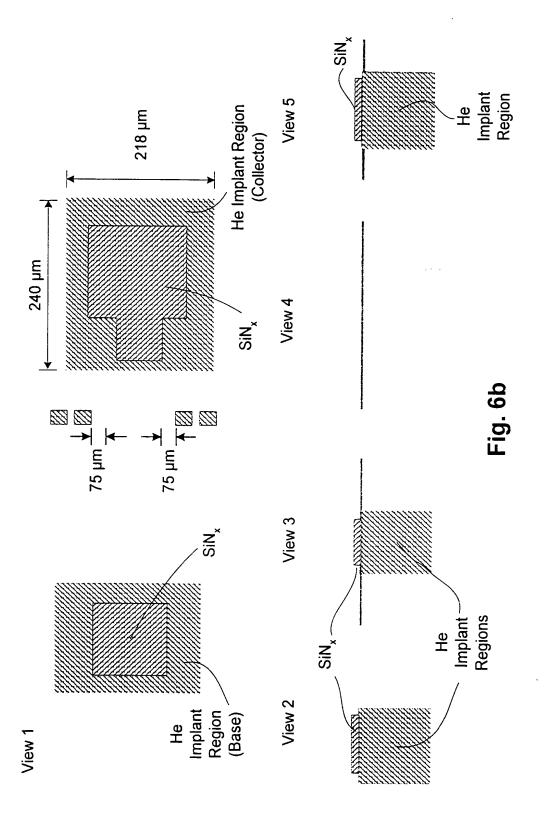


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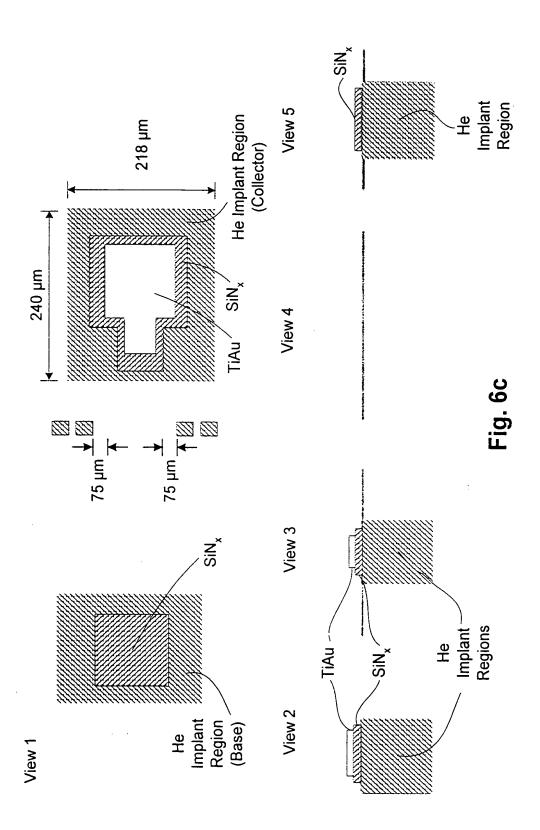




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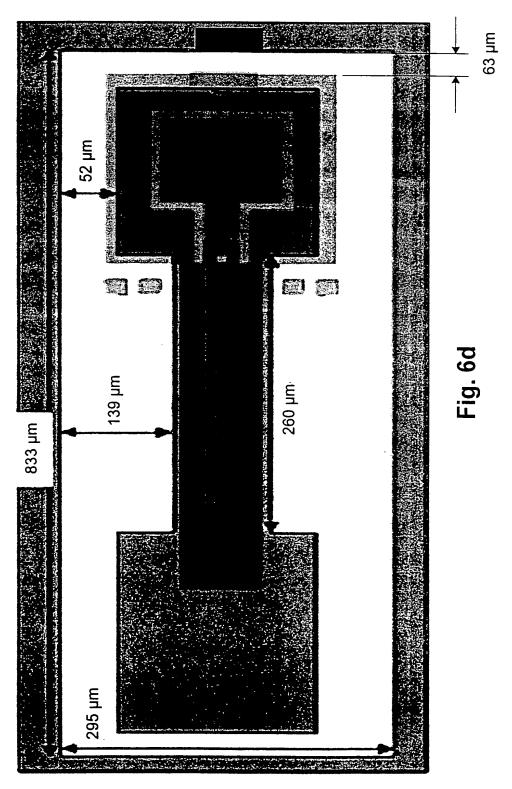
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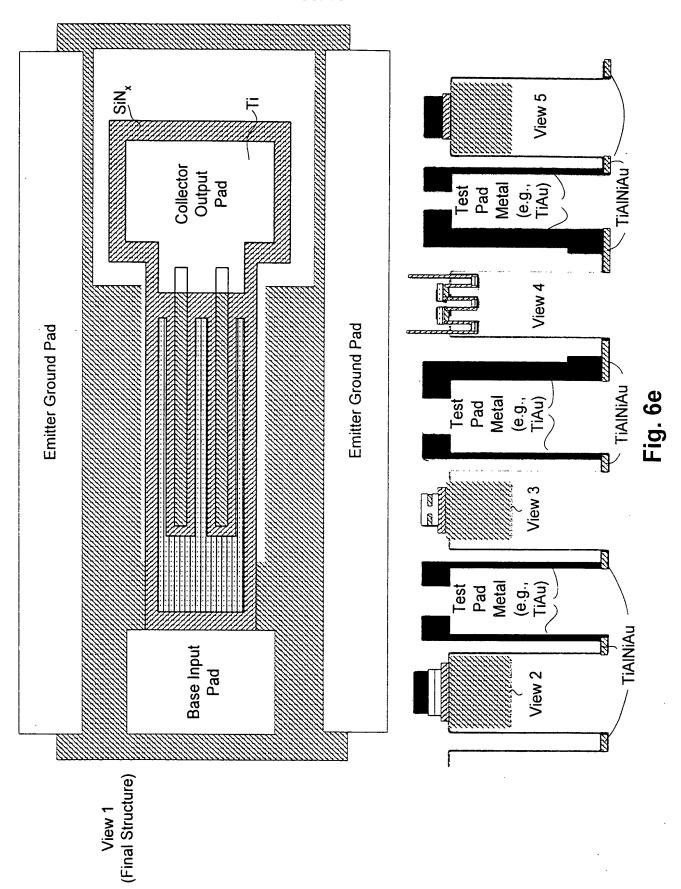
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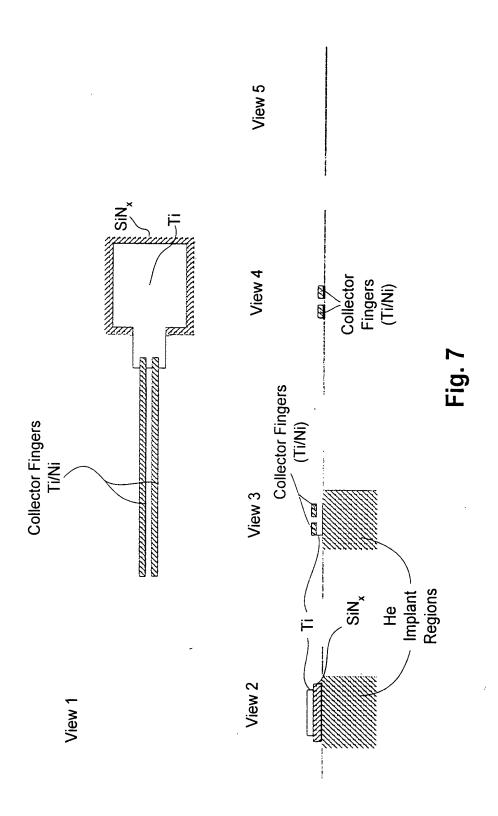
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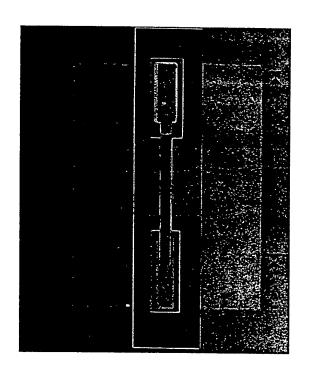
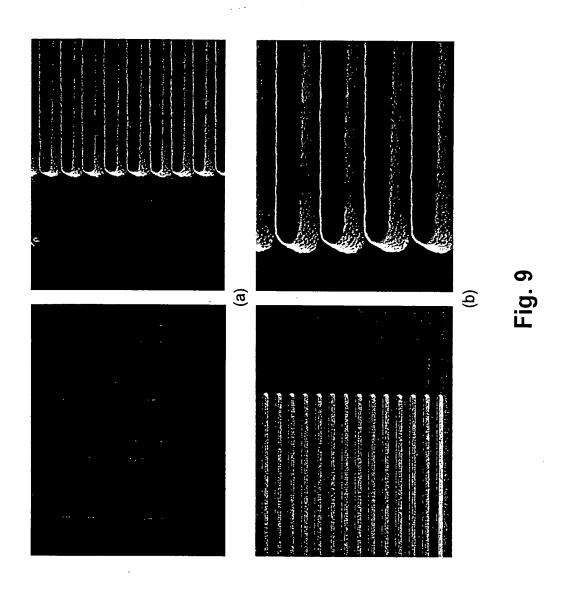
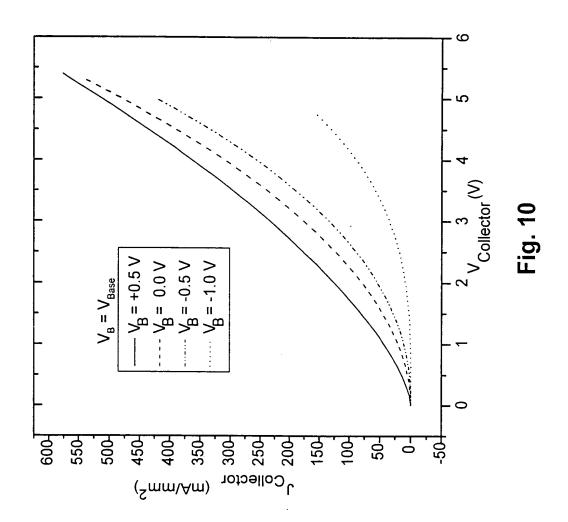


Fig. 8

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